Infineon Technologies - MB96F643RBPMC-GSE1 Datasheet

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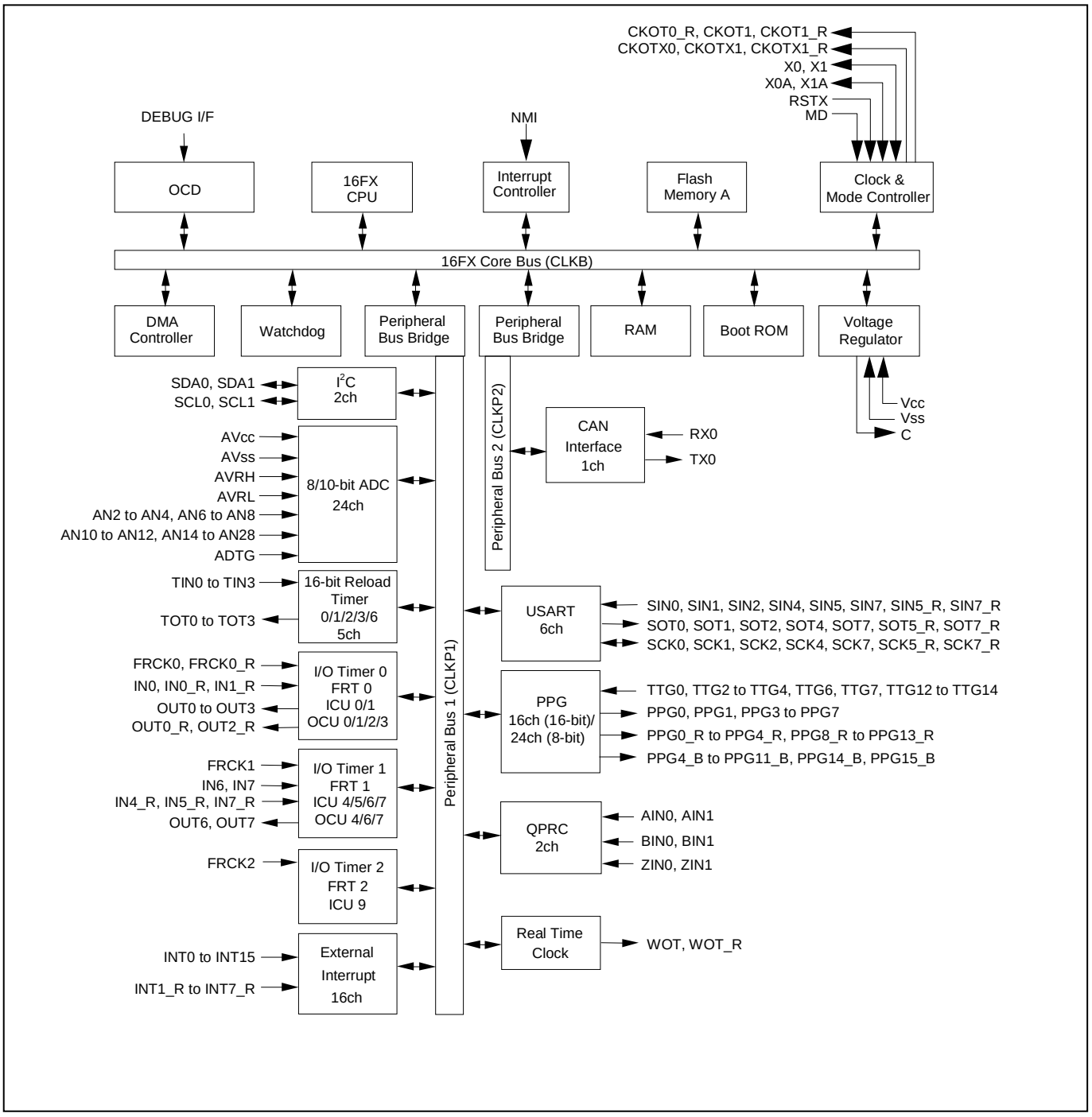
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

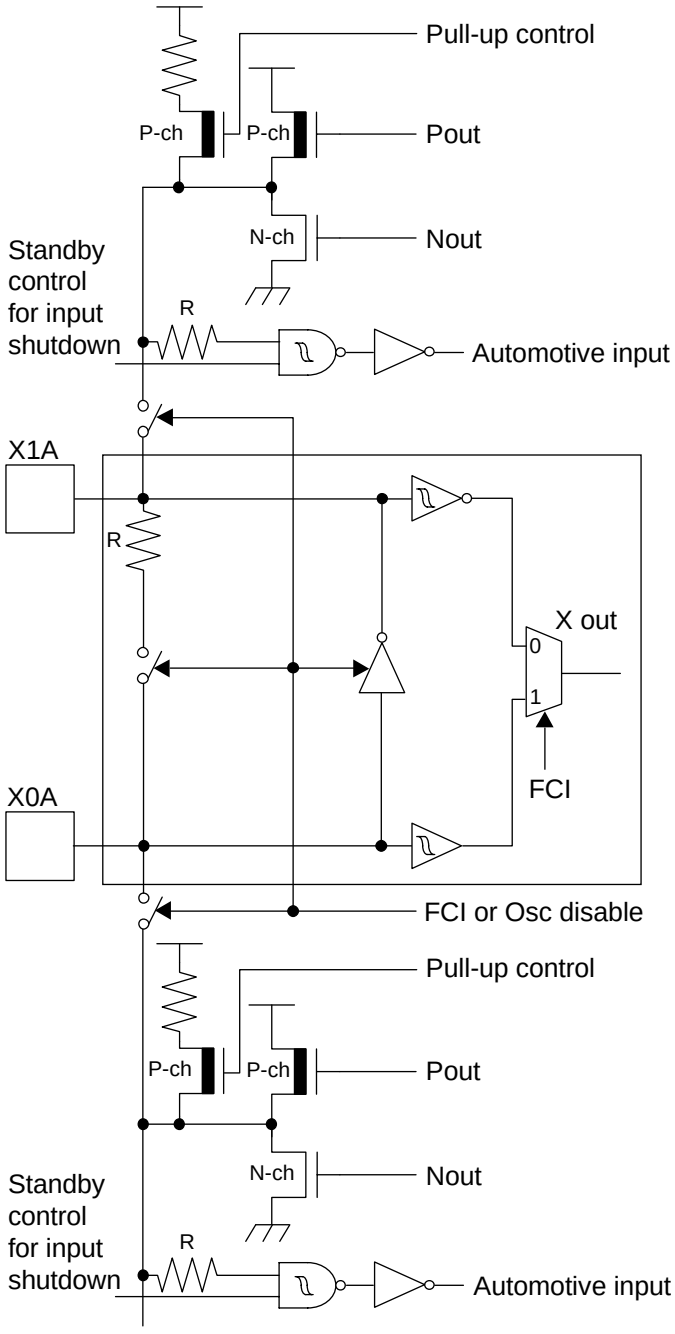
Applications of "Embedded - Microcontrollers"

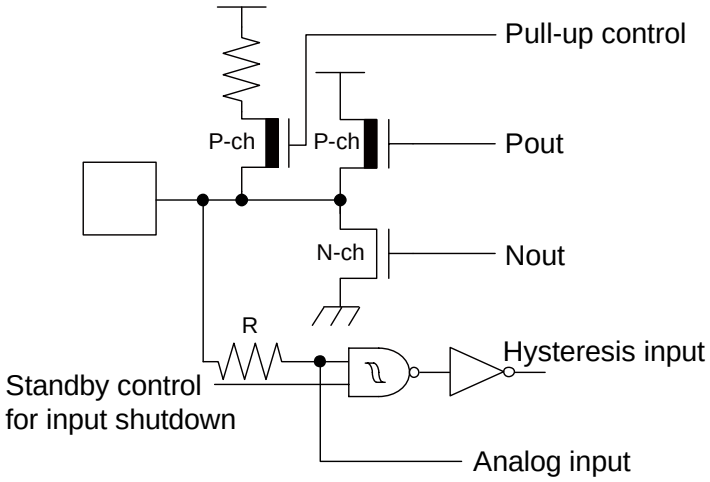
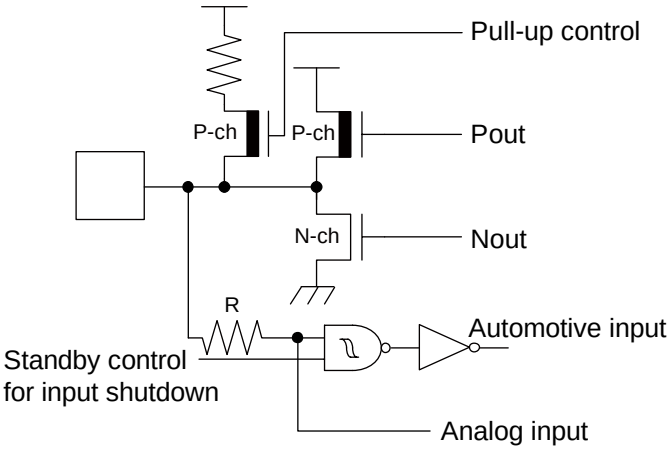
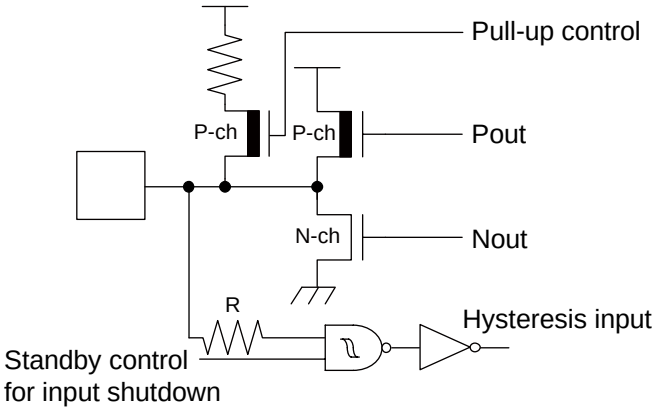
Details	
Product Status	Obsolete
Core Processor	F²MC-16FX
Core Size	16-Bit
Speed	32MHz
Connectivity	CANbus, I²C, LINbus, SCI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	81
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 24x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/mb96f643rbpmc-gse1

2. Block Diagram

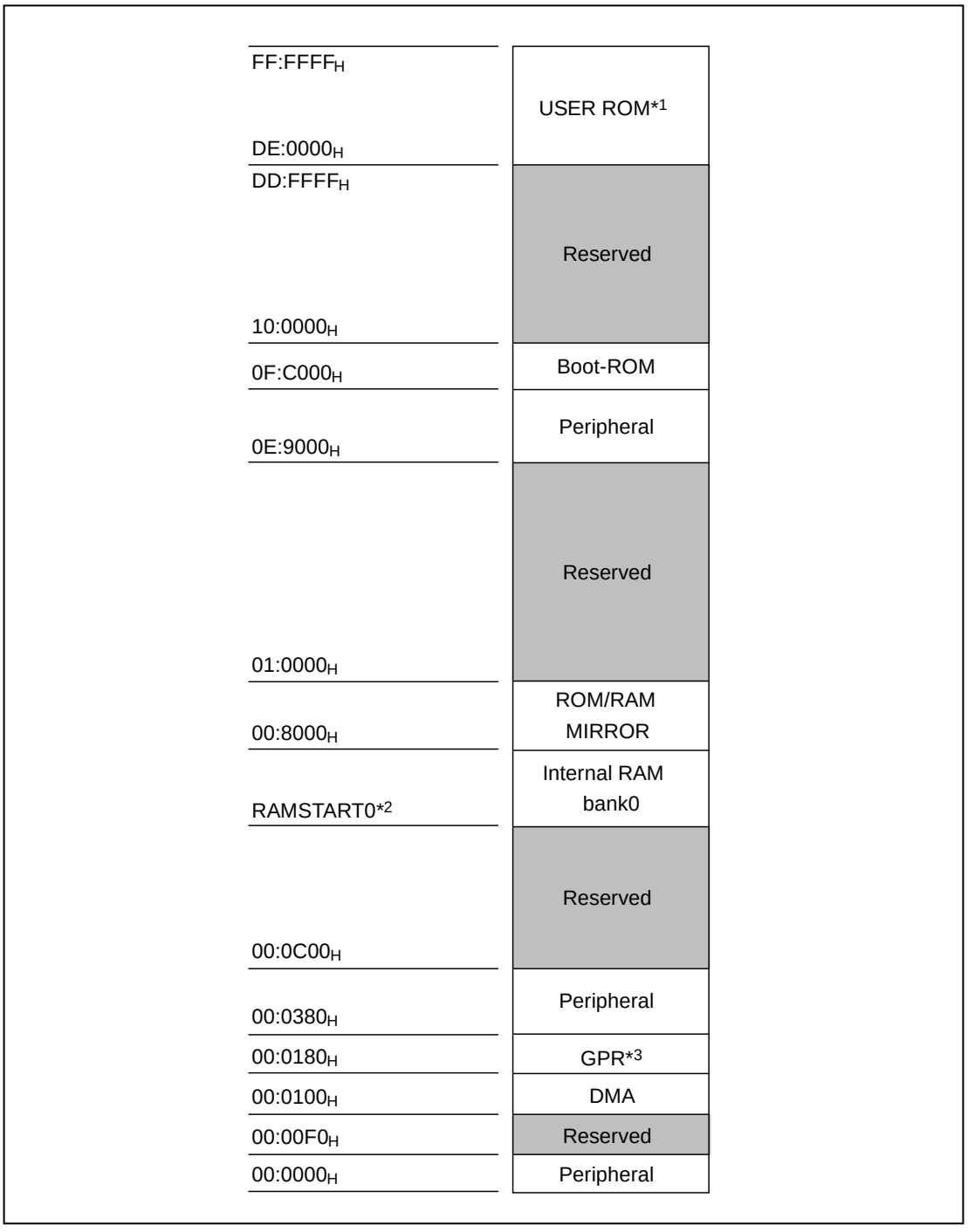


Pin no.	I/O circuit type*	Pin name
39	K	P08_7 / AN23 / PPG7_B
40	K	P09_0 / AN24 / PPG8_R
41	K	P09_1 / AN25 / PPG9_R
42	K	P09_2 / AN26 / PPG10_R
43	K	P09_3 / AN27 / PPG11_R
44	H	P17_1 / PPG12_R
45	H	P17_2 / PPG13_R
46	I	P10_0 / SIN2 / TIN3 / AN28 / INT11
47	H	P10_1 / SOT2 / TOT3
48	M	P10_2 / SCK2 / PPG6
49	H	P10_3 / PPG7
50	Supply	Vcc
51	Supply	Vss
52	O	DEBUG I/F
53	H	P17_0
54	C	MD
55	A	X0
56	A	X1
57	Supply	Vss
58	B	P04_0 / X0A
59	B	P04_1 / X1A
60	C	RSTX
61	H	P11_0
62	H	P11_1 / PPG0_R
63	H	P11_2 / PPG1_R
64	H	P11_3 / PPG2_R
65	H	P11_4 / PPG3_R
66	H	P11_5 / PPG4_R
67	H	P11_6 / FRCK0_R / ZIN1
68	H	P11_7 / IN0_R / AIN1
69	H	P12_0 / IN1_R / BIN1
70	H	P12_3 / OUT2_R
71	H	P12_7 / INT1_R
72	H	P00_0 / INT3_R / FRCK2
73	H	P00_1 / INT4_R
74	H	P00_2 / INT5_R
75	Supply	Vcc
76	Supply	Vss
77	H	P00_3 / INT6_R / PPG8_B

Type	Circuit	Remarks
B		Low-speed oscillation circuit shared with GPIO functionality: • Feedback resistor = approx. 5.0MΩ • GPIO functionality selectable (CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA), Automotive input with input shutdown function and programmable pull-up resistor)

Type	Circuit	Remarks
I		• CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA) • CMOS hysteresis input with input shutdown function • Programmable pull-up resistor • Analog input
K		• CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA) • Automotive input with input shutdown function • Programmable pull-up resistor • Analog input
M		• CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA) • CMOS hysteresis input with input shutdown function • Programmable pull-up resistor

7. Memory Map



*1: For details about USER ROM area, see “User Rom Memory Map For Flash Devices” on the following pages.

*2: For RAMSTART Addresses, see the table on the next page.

*3: Unused GPR banks can be used as RAM area.

GPR: General-Purpose Register

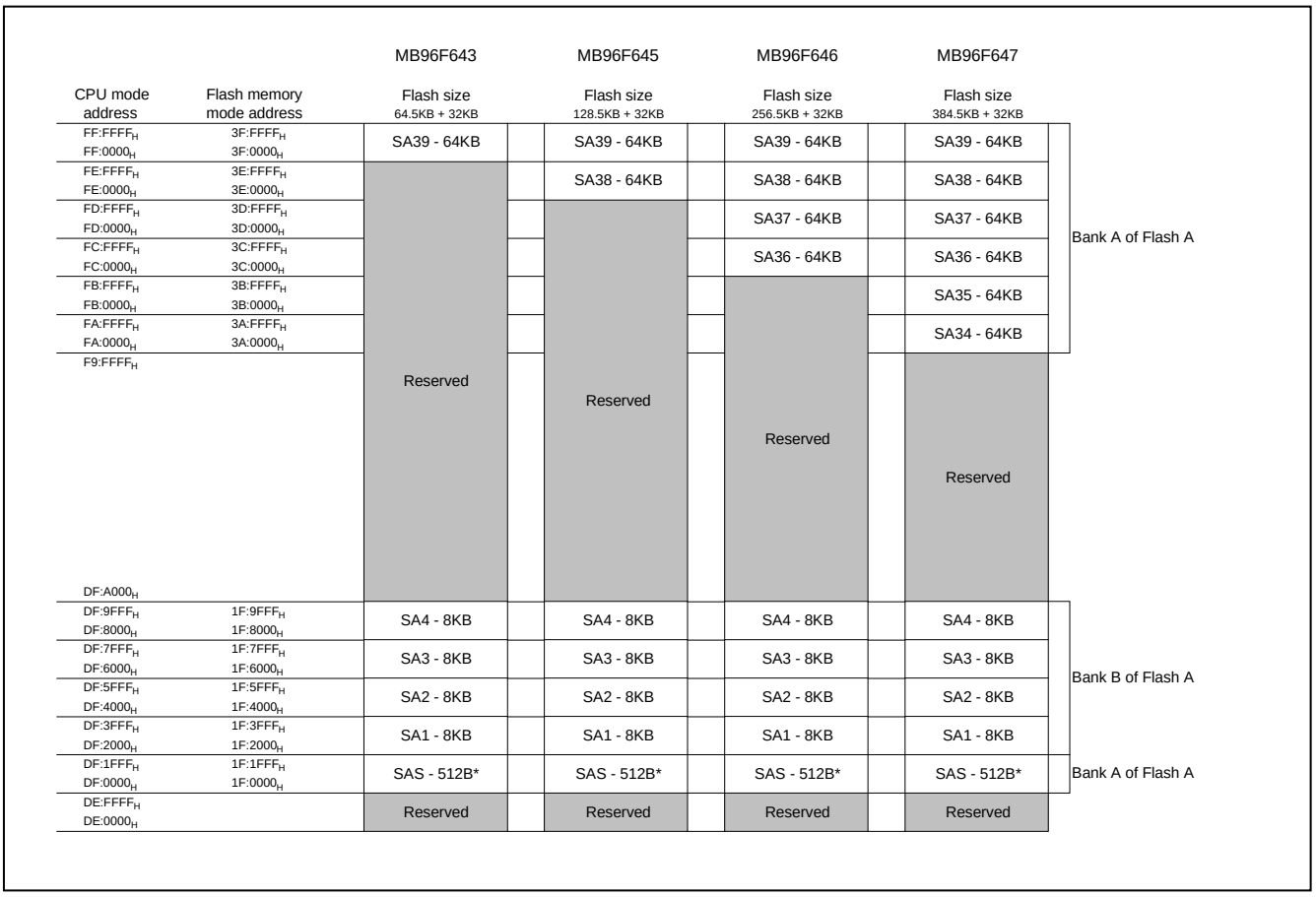
The DMA area is only available if the device contains the corresponding resource.

The available RAM and ROM area depends on the device.

8. RAMSTART Addresses

Devices	Bank 0 RAM size	RAMSTART0
MB96F643	10KB	$00:5A00_H$
MB96F645	16KB	$00:4200_H$
MB96F646	24KB	$00:2200_H$
MB96F647	28KB	$00:1200_H$

9. User Rom Memory Map For Flash Devices



*: Physical address area of SAS-512B is from DF: 0000_H to DF:$01FF_H$.
Others (from DF:0200_H to DF:$1FFF_H$) is mirror area of SAS-512B.
Sector SAS contains the ROM configuration block RCBA at CPU address DF: 0000_H -DF: $01FF_H$.
SAS cannot be used for E^2PROM emulation.

■Precautions Related to Usage of Devices
Cypress semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION: Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

12.2 Precautions for Package Mounting
Package mounting may be either lead insertion type or surface mount type. In either case, for heat resistance during soldering, you should only mount under Cypress's recommended conditions. For detailed information about mount conditions, contact your sales representative.

■Lead Insertion Type
Mounting of lead insertion type packages onto printed circuit boards may be done by two methods: direct soldering on the board, or mounting by using a socket.

Direct mounting onto boards normally involves processes for inserting leads into through-holes on the board and using the flow soldering (wave soldering) method of applying liquid solder. In this case, the soldering process usually causes leads to be subjected to thermal stress in excess of the absolute ratings for storage temperature. Mounting processes should conform to Cypress recommended mounting conditions.

If socket mounting is used, differences in surface treatment of the socket contacts and IC lead surfaces can lead to contact deterioration after long periods. For this reason it is recommended that the surface treatment of socket contacts and IC leads be verified before mounting.

■Surface Mount Type
Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. Cypress recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with Cypress ranking of recommended conditions.

■Lead-Free Packaging
CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

■Storage of Semiconductor Devices
Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent, do the following:

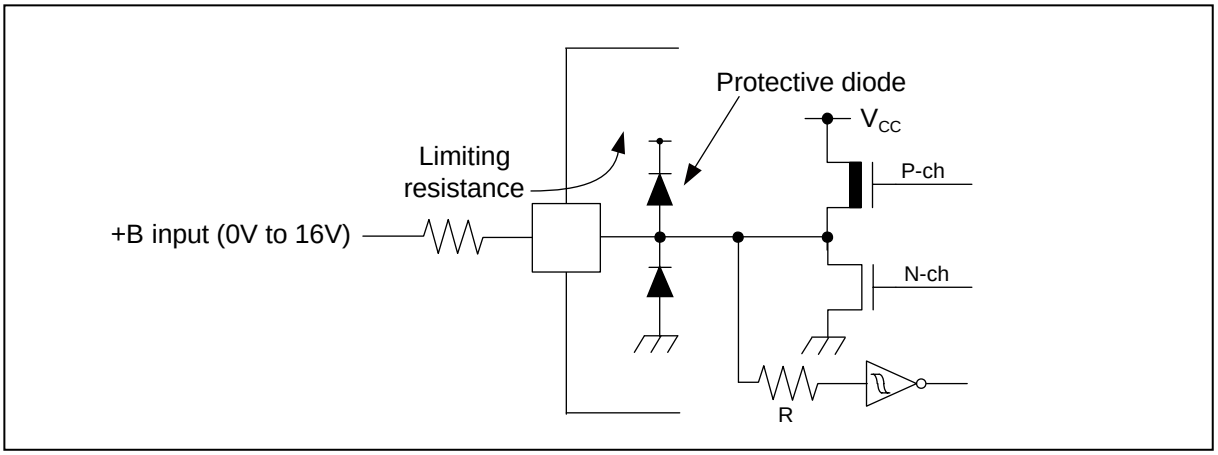
1. Avoid exposure to rapid temperature changes, which cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
2. Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.
   When you open Dry Package that recommends humidity 40% to 70% relative humidity.
3. When necessary, Cypress packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in their aluminum laminate bags for storage.
4. Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

■Baking
Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the Cypress recommended conditions for baking.

Condition: 125°C/24 h

- Note that if the +B input is applied during power-on, the power supply is provided from the pins and the resulting supply voltage may not be sufficient to operate the Power reset.
- The DEBUG I/F pin has only a protective diode against VSS. Hence it is only permitted to input a negative clamping current (4mA). For protection against positive input voltages, use an external clamping diode which limits the input voltage to maximum 6.0V.

- Sample recommended circuits:



*5: The maximum permitted power dissipation depends on the ambient temperature, the air flow velocity and the thermal conductance of the package on the PCB.
The actual power dissipation depends on the customer application and can be calculated as follows:
$P_D = P_{IO} + P_{INT}$
$P_{IO} = \Sigma (V_{OL} \times I_{OL} + V_{OH} \times I_{OH})$ (I/O load power dissipation, sum is performed on all I/O ports)
$P_{INT} = V_{CC} \times (I_{CC} + I_A)$ (internal power dissipation)
I_{CC} is the total core current consumption into V_{CC} as described in the “DC characteristics” and depends on the selected operation mode and clock frequency and the usage of functions like Flash programming.
I_A is the analog current consumption into AV_{CC}.

*6: Worst case value for a package mounted on single layer PCB at specified T_A without air flow.

*7: Write/erase to a large sector in flash memory is warranted with $T_A \leq +105°C$.

WARNING

Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

Parameter	Symbol	Pin name	Conditions	Value			Unit	Remarks
				Min	Typ	Max		
"H" level output voltage	V_{OH4}	4mA type	$4.5V \le V_{CC} \le 5.5V$ $I_{OH} = -4mA$	V_{CC} - 0.5	-	V_{CC}	V	
			$2.7V \le V_{CC} < 4.5V$ $I_{OH} = -1.5mA$					
	V_{OH3}	3mA type	$4.5V \le V_{CC} \le 5.5V$ $I_{OH} = -3mA$	V_{CC} - 0.5	-	V_{CC}	V	
			$2.7V \le V_{CC} < 4.5V$ $I_{OH} = -1.5mA$					
"L" level output voltage	V_{OL4}	4mA type	$4.5V \le V_{CC} \le 5.5V$ $I_{OL} = +4mA$	-	-	0.4	V	
			$2.7V \le V_{CC} < 4.5V$ $I_{OL} = +1.7mA$					
	V_{OL3}	3mA type	$2.7V \le V_{CC} < 5.5V$ $I_{OL} = +3mA$	-	-	0.4	V	
	V_{OLD}	DEBUG I/F	$V_{CC} = 2.7V$ $I_{OL} = +25mA$	0	-	0.25	V	
Input leak current	I_{IL}	Pnn_m	$V_{SS} < V_I < V_{CC}$ AV_{SS}, AVRL < V_I < AV_{CC}, AVRH	- 1	-	+ 1	µA	
Pull-up resistance value	R_{PU}	Pnn_m	$V_{CC} = 5.0V \pm 10\%$	25	50	100	kΩ	
Input capacitance	C_{IN}	Other than C, Vcc, Vss, AVcc, AVss, AVRH, AVRL	-	-	5	15	pF	

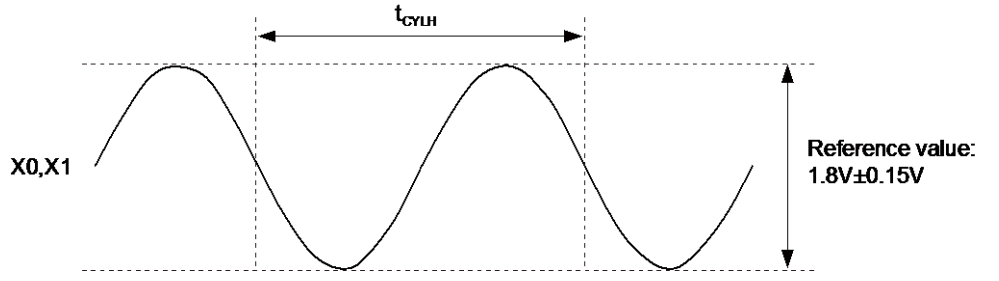
14.4 AC Characteristics

14.4.1 Main Clock Input Characteristics

(V_{CC} = AV_{CC} = 2.7V to 5.5V, VD=1.8V±0.15V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

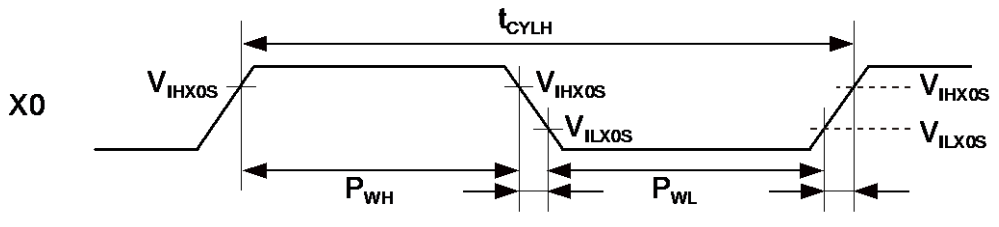
Parameter	Symbol	Pin name	Value			Unit	Remarks
			Min	Typ	Max		
Input frequency	f_C	X0, X1	4	-	8	MHz	When using a crystal oscillator, PLL off
			-	-	8	MHz	When using an opposite phase external clock, PLL off
			4	-	8	MHz	When using a crystal oscillator or opposite phase external clock, PLL on
Input frequency	f_{FCI}	X0	-	-	8	MHz	When using a single phase external clock in “Fast Clock Input mode”, PLL off
			4	-	8	MHz	When using a single phase external clock in “Fast Clock Input mode”, PLL on
Input clock cycle	t_{CYLH}	-	125	-	-	ns	
Input clock pulse width	P_{WH}, P_{WL}	-	55	-	-	ns	

When using the crystal oscillator



The amplitude changes by resistance, capacity which added outside or the difference of the device.

When using the external clock



14.4.3 Built-in RC Oscillation Characteristics

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

Parameter	Symbol	Value			Unit	Remarks
		Min	Typ	Max		
Clock frequency	f_{RC}	50	100	200	kHz	When using slow frequency of RC oscillator
		1	2	4	MHz	When using fast frequency of RC oscillator
RC clock stabilization time	t_{RCSTAB}	80	160	320	µs	When using slow frequency of RC oscillator (16 RC clock cycles)
		64	128	256	µs	When using fast frequency of RC oscillator (256 RC clock cycles)

14.4.4 Internal Clock Timing

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

Parameter	Symbol	Value		Unit
		Min	Max	
Internal System clock frequency (CLKS1 and CLKS2)	f_{CLKS1}, f_{CLKS2}	-	54	MHz
Internal CPU clock frequency (CLKB), Internal peripheral clock frequency (CLKP1)	f_{CLKB}, f_{CLKP1}	-	32	MHz
Internal peripheral clock frequency (CLKP2)	f_{CLKP2}	-	32	MHz

14.4.8 USART Timing

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C, C_L=50pF)

Parameter	Symbol	Pin name	Conditions	4.5V ≤ Vcc <5.5V		2.7V ≤ Vcc < 4.5V		Unit
				Min	Max	Min	Max	
Serial clock cycle time	t_{SCYC}	SCKn	Internal shift clock mode	$4t_{CLKP1}$	-	$4t_{CLKP1}$	-	ns
SCK ↓ → SOT delay time	t_{SLOVI}	SCKn, SOTn		- 20	+ 20	- 30	+ 30	ns
SOT → SCK ↑ delay time	t_{OVSHI}	SCKn, SOTn		$N \times t_{CLKP1}$ – 20*	-	$N \times t_{CLKP1}$ – 30*	-	ns
SIN → SCK ↑ setup time	t_{IVSHI}	SCKn, SINn		t_{CLKP1} + 45	-	t_{CLKP1} + 55	-	ns
SCK ↑ → SIN hold time	t_{SHIXI}	SCKn, SINn		0	-	0	-	ns
Serial clock "L" pulse width	t_{SLSH}	SCKn	External shift clock mode	t_{CLKP1} + 10	-	t_{CLKP1} + 10	-	ns
Serial clock "H" pulse width	t_{SHSL}	SCKn		t_{CLKP1} + 10	-	t_{CLKP1} + 10	-	ns
SCK ↓ →SOT delay time	t_{SLOVE}	SCKn, SOTn		-	$2t_{CLKP1}$ + 45	-	$2t_{CLKP1}$ + 55	ns
SIN → SCK ↑ setup time	t_{IVSHE}	SCKn, SINn		$t_{CLKP1}/2$ + 10	-	$t_{CLKP1}/2$ + 10	-	ns
SCK ↑ → SIN hold time	t_{SHIXE}	SCKn, SINn		t_{CLKP1} + 10	-	t_{CLKP1} + 10	-	ns
SCK fall time	t_F	SCKn		-	20	-	20	ns
SCK rise time	t_R	SCKn		-	20	-	20	ns

Notes:

- AC characteristic in CLK synchronized mode.
- C_L is the load capacity value of pins when testing.
- Depending on the used machine clock frequency, the maximum possible baud rate can be limited by some parameters. These parameters are shown in “MB96600 series HARDWARE MANUAL”.
- t_{CLKP1} indicates the peripheral clock 1 (CLKP1), Unit: ns
- These characteristics only guarantee the same relocate port number.
  For example, the combination of SCKn and SOTn_R is not guaranteed.

*: Parameter N depends on t_{SCYC} and can be calculated as follows:

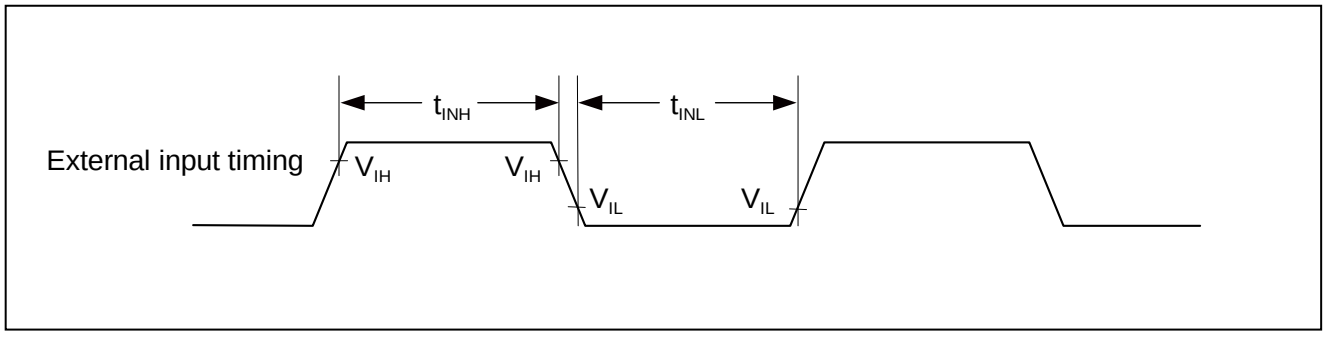
- If $t_{SCYC} = 2 \times k \times t_{CLKP1}$, then N = k, where k is an integer > 2
- If $t_{SCYC} = (2 \times k + 1) \times t_{CLKP1}$, then N = k + 1, where k is an integer > 1

14.4.9 External Input Timing

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

Parameter	Symbol	Pin name	Value		Unit	Remarks
			Min	Max		
Input pulse width	t_{INH}, t_{INL}	Pnn_m	$2t_{CLKP1}$ +200 (t_{CLKP1}= $1/f_{CLKP1}$)*	-	ns	General Purpose I/O
		ADTG				A/D Converter trigger input
		TINn				Reload Timer
		TTGn				PPG trigger input
		FRCKn, FRCKn_R				Free-Running Timer input clock
		INn, INn_R				Input Capture
		AINn, BINn, ZINn				Quadrature Position/Revolution Counter
		INTn, INTn_R	200	-	ns	External Interrupt
		NMI				Non-Maskable Interrupt

*: t_{CLKP1} indicates the peripheral clock1 (CLKP1) cycle time except stop when in stop mode.



14.4.10 I^2C Timing

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

Parameter	Symbol	Conditions	Typical mode		High-speed mode*4		Unit
			Min	Max	Min	Max	
SCL clock frequency	f_{SCL}	C_L = 50pF, R = (Vp/I_{OL})*1	0	100	0	400	kHz
(Repeated) START condition hold time SDA ↓ → SCL ↓	t_{HDSTA}		4.0	-	0.6	-	µs
SCL clock "L" width	t_{LOW}		4.7	-	1.3	-	µs
SCL clock "H" width	t_{HIGH}		4.0	-	0.6	-	µs
(Repeated) START condition setup time SCL ↑ →SDA ↓	t_{SUSTA}		4.7	-	0.6	-	µs
Data hold time SCL ↓ → SDA ↓ ↑	t_{HDDAT}		0	3.45*2	0	0.9*3	µs
Data setup time SDA ↓ ↑ → SCL ↑	t_{SUDAT}		250	-	100	-	ns
STOP condition setup time SCL ↑ → SDA ↑	t_{SUSTO}		4.0	-	0.6	-	µs
Bus free time between "STOP condition" and "START condition"	t_{BUS}		4.7	-	1.3	-	µs
Pulse width of spikes which will be suppressed by input noise filter	t_{SP}	-	0	(1-1.5) × t_{CLKP1}*5	0	(1-1.5) × t_{CLKP1}*5	ns

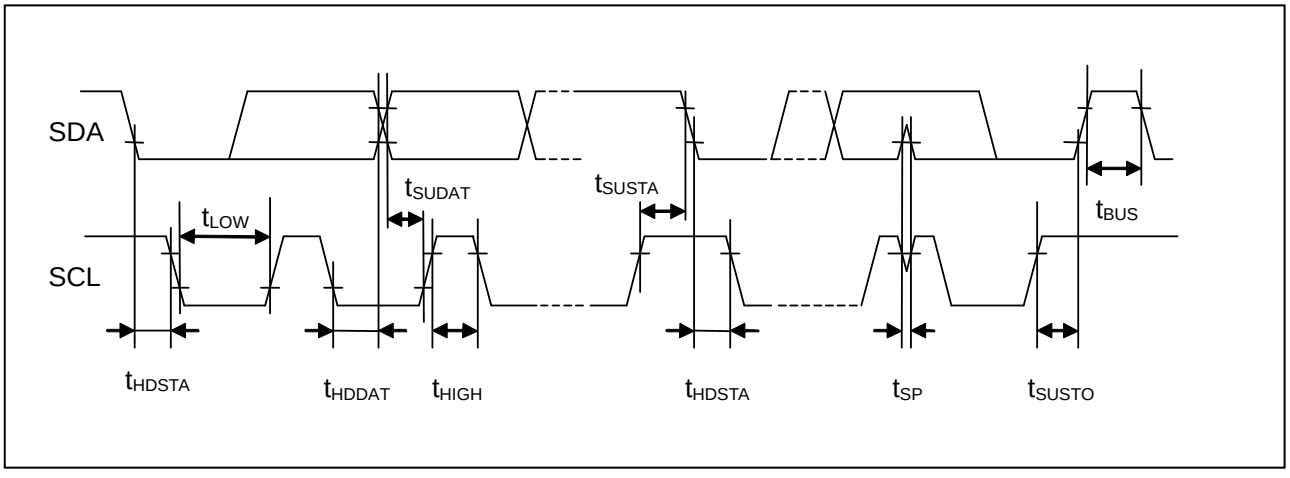
*1: R and C_L represent the pull-up resistance and load capacitance of the SCL and SDA lines, respectively. Vp indicates the power supply voltage of the pull-up resistance and I_{OL} indicates V_{OL} guaranteed current.

*2: The maximum t_{HDDAT} only has to be met if the device does not extend the "L" width (t_{LOW}) of the SCL signal.

*3: A high-speed mode I^2C bus device can be used on a standard mode I^2C bus system as long as the device satisfies the requirement of "t_{SUDAT} ≥ 250ns".

*4: For use at over 100 kHz, set the peripheral clock1 (CLKP1) to at least 6MHz.

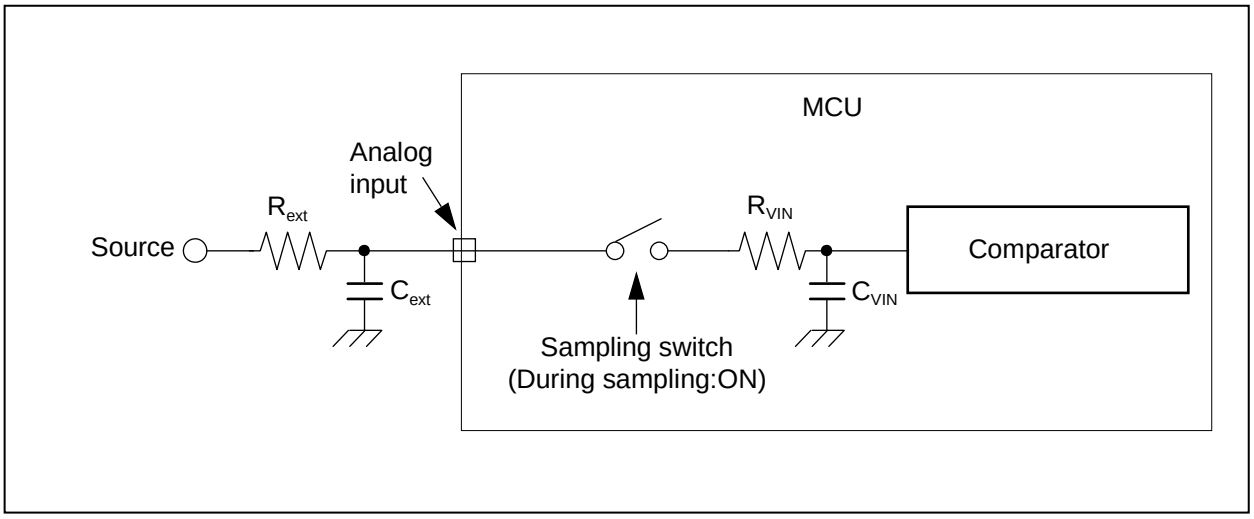
*5: t_{CLKP1} indicates the peripheral clock1 (CLKP1) cycle time.



14.5.2 Accuracy and Setting of the A/D Converter Sampling Time

If the external impedance is too high or the sampling time too short, the analog voltage charged to the internal sample and hold capacitor is insufficient, adversely affecting the A/D conversion precision.

To satisfy the A/D conversion precision, a sufficient sampling time must be selected. The required sampling time (Tsamp) depends on the external driving impedance R_{ext}, the board capacitance of the A/D converter input pin C_{ext} and the AV_{CC} voltage level. The following replacement model can be used for the calculation:



R_{ext}: External driving impedance

C_{ext}: Capacitance of PCB at A/D converter input

C_{VIN}: Analog input capacity (I/O, analog switch and ADC are contained)

R_{VIN}: Analog input impedance (I/O, analog switch and ADC are contained)

The following approximation formula for the replacement model above can be used:
$Tsamp = 7.62 \times (R_{ext} \times C_{ext} + (R_{ext} + R_{VIN}) \times C_{VIN})$

- Do not select a sampling time below the absolute minimum permitted value.
  ($0.5\mu s$ for $4.5V \le AV_{CC} \le 5.5V$, $1.2\mu s$ for $2.7V \le AV_{CC} < 4.5V$)
- If the sampling time cannot be sufficient, connect a capacitor of about $0.1\mu F$ to the analog input pin.
- A big external driving impedance also adversely affects the A/D conversion precision due to the pin input leakage current IIL (static current before the sampling switch) or the analog input leakage current IAIN (total leakage current of pin input and comparator during sampling). The effect of the pin input leakage current IIL cannot be compensated by an external capacitor.
- The accuracy gets worse as |AVRH - AVRL| becomes smaller.

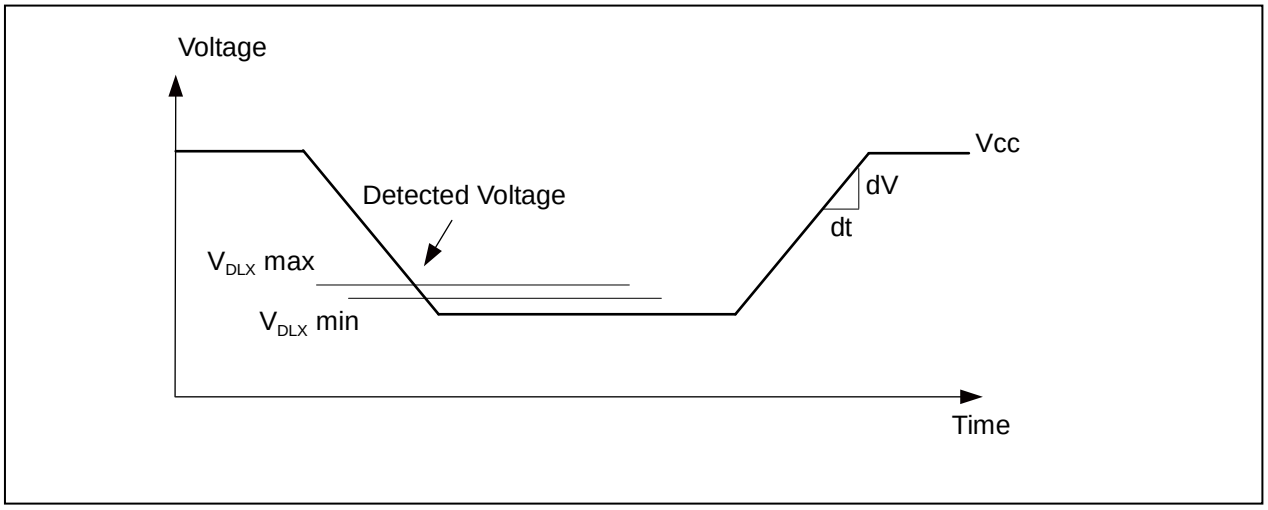
14.6 Low Voltage Detection Function Characteristics

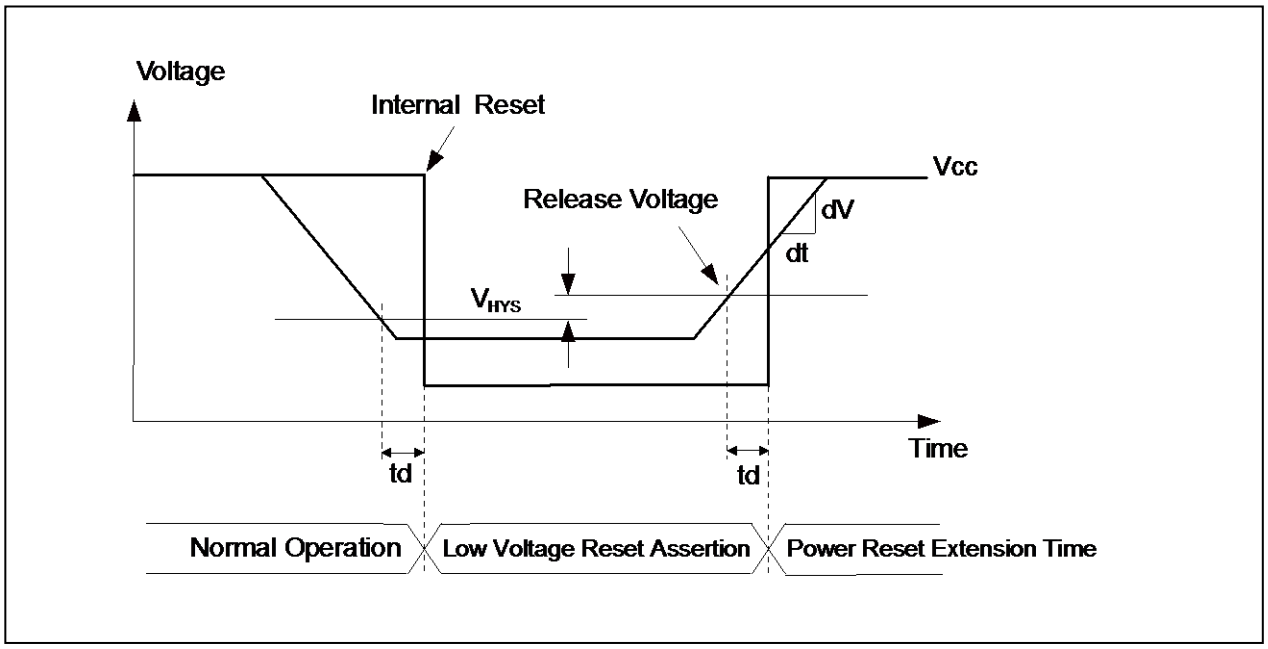
(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

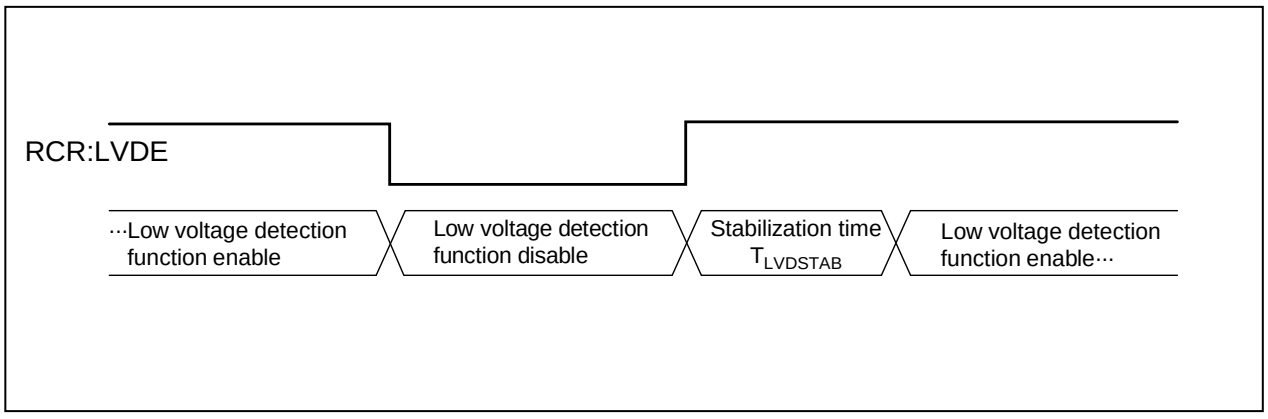
Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Detected voltage*1	V_{DL0}	CILCR:LVL = 0000_B	2.70	2.90	3.10	V
	V_{DL1}	CILCR:LVL = 0001_B	2.79	3.00	3.21	V
	V_{DL2}	CILCR:LVL = 0010_B	2.98	3.20	3.42	V
	V_{DL3}	CILCR:LVL = 0011_B	3.26	3.50	3.74	V
	V_{DL4}	CILCR:LVL = 0100_B	3.45	3.70	3.95	V
	V_{DL5}	CILCR:LVL = 0111_B	3.73	4.00	4.27	V
	V_{DL6}	CILCR:LVL = 1001_B	3.91	4.20	4.49	V
Power supply voltage change rate*2	dV/dt	-	- 0.004	-	+ 0.004	V/µs
Hysteresis width	V_{HYS}	CILCR:LVHYS=0	-	-	50	mV
		CILCR:LVHYS=1	80	100	120	mV
Stabilization time	$T_{LVDSTAB}$	-	-	-	75	µs
Detection delay time	t_d	-	-	-	30	µs

*1: If the power supply voltage fluctuates within the time less than the detection delay time (t_d), there is a possibility that the low voltage detection will occur or stop after the power supply voltage passes the detection range.

*2: In order to perform the low voltage detection at the detection voltage (V_{DLX}), be sure to suppress fluctuation of the power supply voltage within the limits of the change ration of power supply voltage.




Voltage
Internal Reset
Vcc
Release Voltage
dV
dt
V_{HYS}
Time
td
td
Normal Operation
Low Voltage Reset Assertion
Power Reset Extension Time


RCR:LVDE
···Low voltage detection function enable
Low voltage detection function disable
Stabilization time $T_{LVDSTAB}$
Low voltage detection function enable···

14.7 Flash Memory Write/Erase Characteristics

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = 0V, T_A = - 40°C to + 125°C)

Parameter		Conditions	Value			Unit	Remarks
			Min	Typ	Max		
Sector erase time	Large Sector	T_A ≤ + 105°C	-	1.6	7.5	s	Includes write time prior to internal erase.
	Small Sector	-	-	0.4	2.1	s	
	Security Sector	-	-	0.31	1.65	s	
Word (16-bit) write time	Large Sector	T_A ≤ + 105°C	-	25	400	µs	Not including system-level overhead time.
	Small Sector	-	-	25	400	µs	
Chip erase time		T_A ≤ + 105°C	-	11.51	55.05	s	Includes write time prior to internal erase.

Note:

While the Flash memory is written or erased, shutdown of the external power (V_{CC}) is prohibited. In the application system where the external power (V_{CC}) might be shut down while writing or erasing, be sure to turn the power off by using a low voltage detection function.

To put it concrete, change the external power in the range of change ration of power supply voltage (-0.004V/µs to +0.004V/µs) after the external power falls below the detection voltage (V_{DLX})[*1].

Write/Erase cycles and data hold time

Write/Erase cycles (cycle)	Data hold time (year)
1,000	20 [*2]
10,000	10 [*2]
100,000	5 [*2]

*1: See "14.6 Low Voltage Detection Function Characteristics".

*2: This value comes from the technology qualification (using Arrhenius equation to translate high temperature measurements into normalized value at + 85°C).

16. Ordering Information

MCU with CAN controller

Part number	Flash memory	Package*
MB96F643RBPMC-GSE1	Flash A (96.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F643RBPMC-GSE2		
MB96F645RBPMC-GSE1	Flash A (160.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F645RBPMC-GSE2		
MB96F646RBPMC-GSE1	Flash A (288.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F646RBPMC-GSE2		
MB96F647RBPMC-GSE1	Flash A (416.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F647RBPMC-GSE2		

*: For details about package, see "Package Dimension".

MCU without CAN controller

Part number	Flash memory	Package*
MB96F643ABPMC-GSE1	Flash A (96.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F643ABPMC-GSE2		
MB96F645ABPMC-GSE1	Flash A (160.5KB)	100-pin plastic LQFP (FPT-100P-M20)
MB96F645ABPMC-GSE2		

*: For details about package, see "Package Dimension".